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cont.
layer, further wherein thickness of said nonconductive layer being arranged above the wiring layer is thicker than that of being arranged above the insulating layer.

16. (Twice Amended) A semiconductor device, comprising:

a substrate;

a first insulating layer covering a surface of the substrate;

a first wiring layer including a plurality of wiring patterns separate from each other embedded on an upper surface of the first insulating layer, the first wiring layer including a first material; and

a nonconductive layer contacting the first wiring layer, and contacting and covering the first insulating layer,

wherein a top of the first wiring layer is not higher than a top of the first insulating layer, and a thickness of said nonconductive layer being arranged above the wiring layer is thicker than that of being arranged above the insulating layer.

17. (Twice Amended) A semiconductor device, comprising:

a substrate;

a first insulating layer covering a surface of the substrate;

a first wiring layer including a plurality of wiring patterns separate from each other embedded on an upper surface of the first insulating layer; and

a nonconductive layer contacting the first wiring layer, and contacting and covering the first insulating layer, the nonconductive layer includes oxygen ions,

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cancel* wherein a top of the first wiring layer is not higher than a top of the first insulating layer,
and a thickness of said nonconductive layer being arranged above the wiring layer is thicker than
that of being arranged above the insulating layer.

18. (Twice Amended) A semiconductor device, comprising:
- a substrate,
 - a first insulating layer covering a surface of the substrate;
 - a first wiring layer including a plurality of wiring patterns separate from each other and
embedded on an upper surface of the first insulating layer; and
 - a nonconductive layer that includes oxygen ions contacting the first wiring layer, and
contacting and covering the first insulating layer,
- wherein at least one of the wiring patterns includes at least one capacitor formed therein.
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